



Claims

1. Transistor comprising elements of a bipolar static induction transistor: a gate, a source, a channel and electrodes, and besides one of channels of multielement structure is thicker than other channels, said channel is connected to a separate electrode -- on each of sides of a lightly doped substrate.

C12

2. Transistor as claimed in claim 1 wherein an epitaxial layer the same conductivity type with the impurity concentration of about 10.17 cm^{-3} is disposed on each of sides of said lightly doped substrate; said gate, said source and said channels are disposed in said epitaxial layer.

AUTHOR:

Edlin
01.23.2003

EDLIN S.D.

RECEIVED
JAN 28 2003
TECHNOLOGY CENTER 2800

RECEIVED
JAN 28 2003
TECHNOLOGY CENTER 2800